

SHEET 1 OF 1

FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT					ATTORNEY DOCKET NO.: ASC-049C1 APPLICANT(S): Fitzgerald SERIAL NO.: 10/774,890 FILING DATE: February 9, 2004 GROUP: 2818				
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
							FAX RECEIVED		
							JUN 24 2005		
							OFFICE OF PETITIONS		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
MF	C102	C. Rosenblad, et al., "Strain relaxation of graded SiGe buffers grown at very high rates," <u>Materials Science and Engineering</u> , B71 (2000), pp. 20-23.							
MF	C103	E.A. Fitzgerald, et al., "Dislocations in Relaxed SiGe/Si Heterostructures," <u>Phys. Stat. Sol.</u> , (a) 171 (1999) pp. 227-238							
EXAMINER	<i>McAlliston</i>				DATE CONSIDERED			07/01/05	
VER 9/00									

FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		ATTORNEY DOCKET NO.: ASC-049C1 APPLICANT(S): Fitzgerald SERIAL NO.: 10/774,890 FILING DATE: February 9, 2004 GROUP: 2818					
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>MS</i>	A191	2003/0080361 A1	05/01/2003	Murthy et al.			
<i>MS</i>	A192	5,821,577	10/13/1998	Crabbé et al.			
<i>MS</i>	A193	6,350,311 B1	02/26/2002	Chin et al.			
OTHER ART, JOURNAL ARTICLES, ETC.							
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)						
<i>MS</i>	C123	Examination Report for European Patent Application No. 98 931 529.6-2203, dated January 10, 2002, 4 pages.					
<i>MS</i>	C124	Examination Report for European Patent Application No. 98 931 529.6-2203, dated May 9, 2003, 5 pages.					
<i>MS</i>	C125	Examination Report for European Patent Application No. 01 973 651.1-1528, dated March 22, 2004, 3 pages.					
<i>MS</i>	C126	Examination Report for European Patent Application No. 01 989 893.1-1235, dated August 16, 2004, 5 pages.					
<i>MS</i>	C127	Examination Report for European Patent Application No. 01 973 651.1-1528, dated November 12, 2004, 9 pages.					
<i>MS</i>	C128	Examination Report for European Patent Application No. 02 709 406.9-2203, dated May 11, 2004, 3 pages.					
<i>MS</i>	C129	Examination Report for European Patent Application No. 02 709 406.9-2203, dated March 24, 2005, 5 pages.					
<i>MS</i>	C130	International Search Report for Patent Application No. PCT/US 98/13076, dated October 27, 1998, 2 pages.					
<i>MS</i>	C131	Notice of Preliminary Rejection for Korean Patent Application No. 10-1999-7012279, dated February 21, 2002, 2 pages (English translation attached).					
<i>MS</i>	C132	Notice of Final Rejection for Korean Patent Application No. 10-1999-7012279, dated February 25, 2003 2 pages (English translation attached).					
<i>MS</i>	C133	Klauck et al., "Thermal stability of undoped strained Si channel SiGe heterostructures," Applied Physics Letter, No. 68, April 1, 1996, pgs. 1975-1977.					
<i>MS</i>	C134	Rim et al., "Enhanced Hole Mobilities in Surface-channel Strained-Si- <i>p</i> -MOSFETs," IEEE (1995), pg. 20.3.1-20.3.4.					
EXAMINER		<i>Malheon</i>		DATE CONSIDERED		<i>7/21/05</i>	